

Description

The AO3416 is the high cell density trenched N-ch MOSFETs, which provides excellent R_{DS(ON)} and efficiency for most of the small power switching and load switch applications.

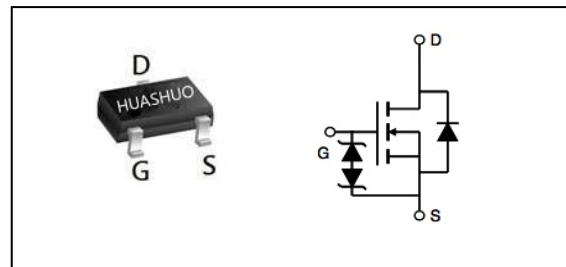
The AO3416 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent C_{dv/dt} effect decline
- Advanced high cell density Trench technology
- ESD Protected 2KV

Product Summary

V _{DS}	20	V
R _{DS(ON),TYP}	18	mΩ
I _D	6	A

SOT23 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±8	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 4.5V ¹	6	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 4.5V ¹	5.2	A
I _{DM}	Pulsed Drain Current ²	30	A
P _D @T _A =25°C	Total Power Dissipation ³	0.72	W
P _D @T _A =70°C	Total Power Dissipation ³	0.46	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	145	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.018	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =6A	---	15	22	mΩ
		V _{GS} =2.5V, I _D =5A	---	18	26	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.5	0.7	1.2	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-3.1	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =16V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±8V, V _{DS} =0V	---	---	±10	uA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =7A	---	50	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =10V, V _{GS} =4.5V, I _D =4A	---	10.6	---	nC
Q _{gs}	Gate-Source Charge		---	4.2	---	
Q _{gd}	Gate-Drain Charge		---	2.6	---	
T _{d(on)}	Turn-On Delay Time	V _{DS} =10V, V _{GS} =4.5V, R _G =3.3Ω I _D =4A	---	280	---	ns
T _r	Rise Time		---	340	---	
T _{d(off)}	Turn-Off Delay Time		---	3.76	---	
T _f	Fall Time		---	2.24	---	
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	1300	---	pF
C _{oss}	Output Capacitance		---	175	---	
C _{rss}	Reverse Transfer Capacitance		---	88	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

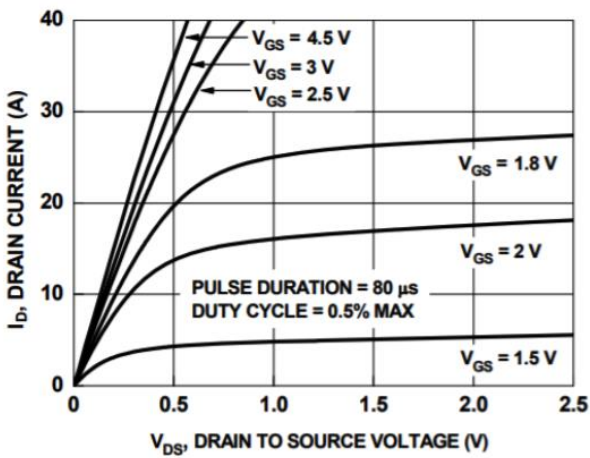


Figure 1. On Region Characteristics

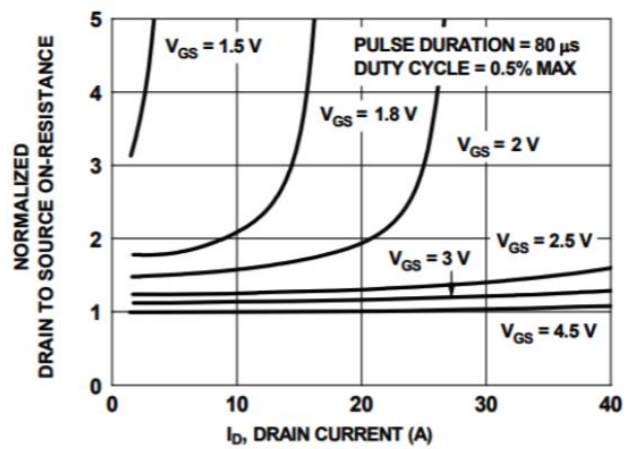


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

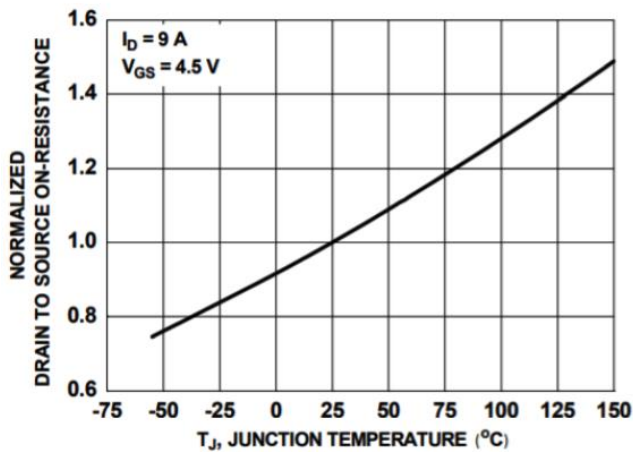


Figure 3. Normalized On Resistance vs Junction Temperature

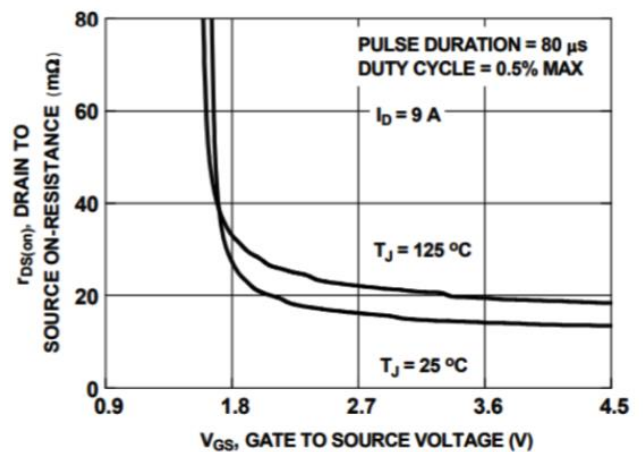


Figure 4. On-Resistance vs Gate to Source Voltage

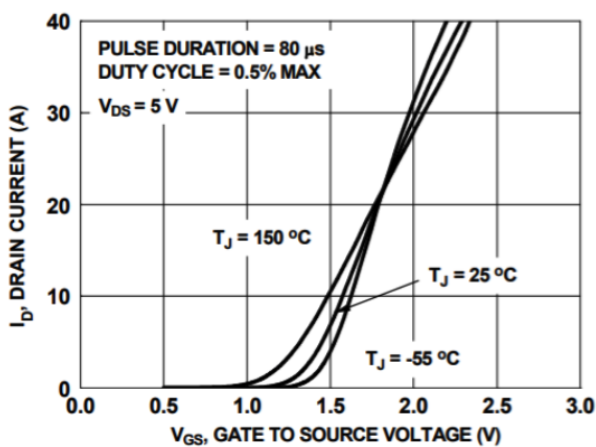


Figure 5. Transfer Characteristics

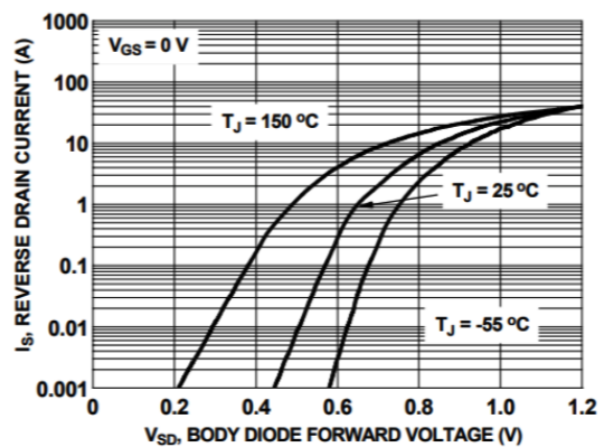


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

N-Ch 20V Fast Switching MOSFETs

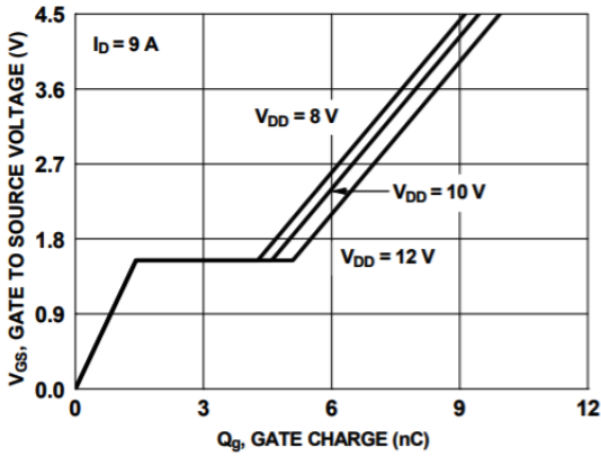


Figure 7. Gate Charge Characteristics

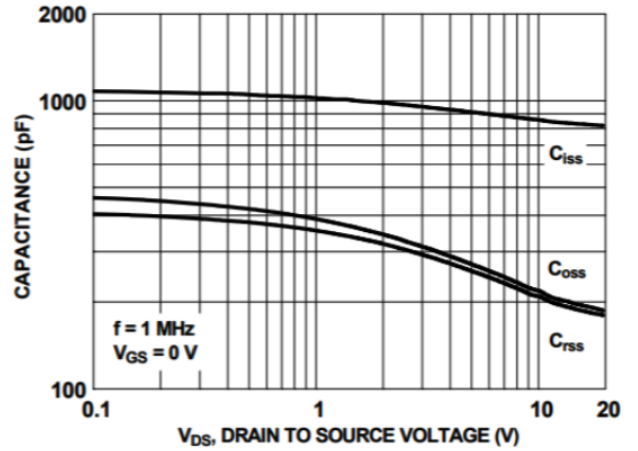


Figure 8. Capacitance vs Drain to Source Voltage

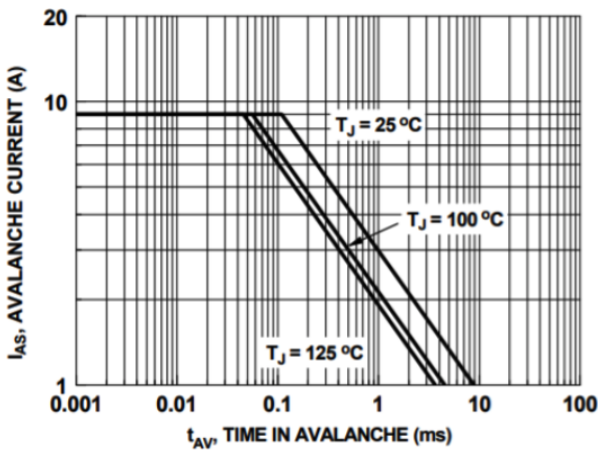


Figure 9. Unclamped Inductive Switching Capability

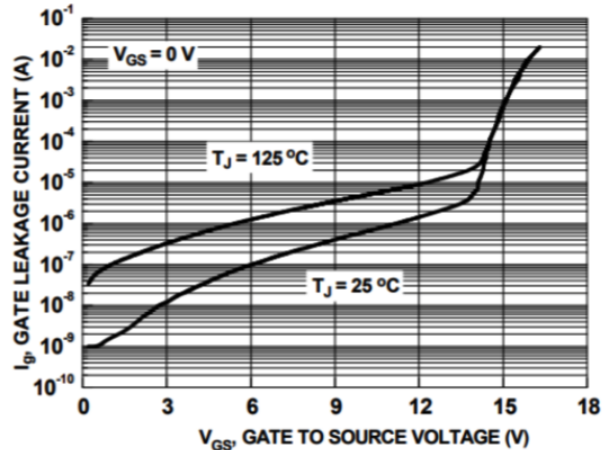


Figure 10. Gate Leakage Current vs Gate to Source Voltage

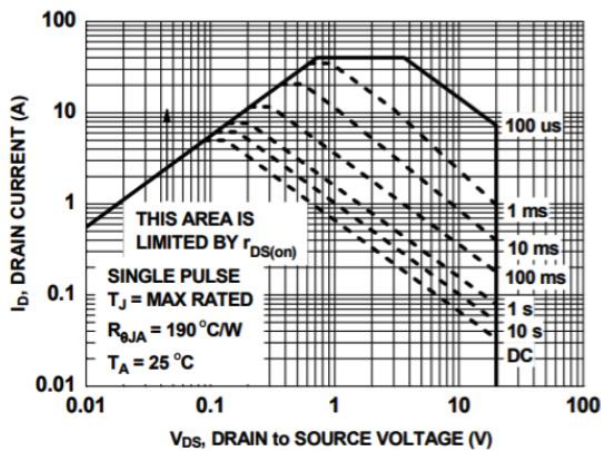


Figure 11. Forward Bias Safe Operating Area

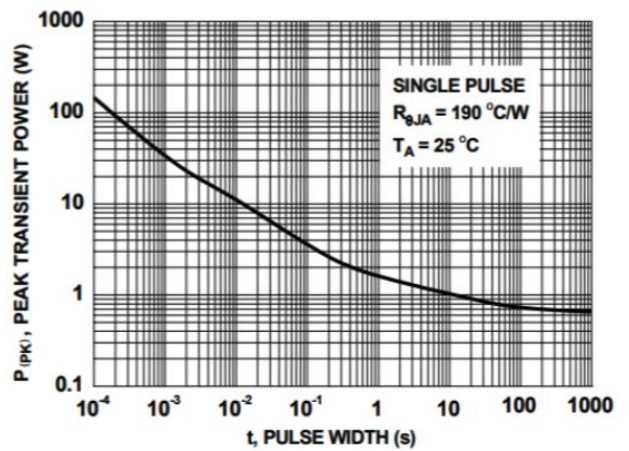
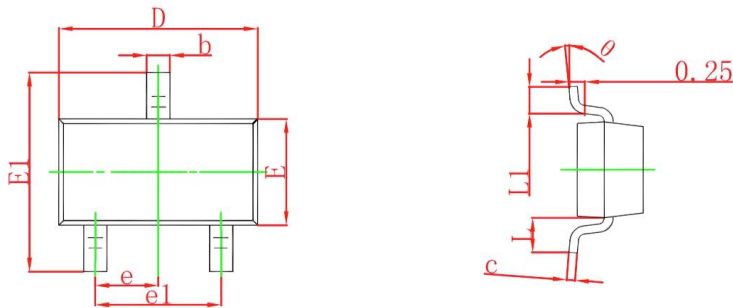


Figure 12. Single Pulse Maximum Power Dissipation

Ordering Information

Part Number	Package code	Packaging
AO3416	SOT-23	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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